

1. Scope :

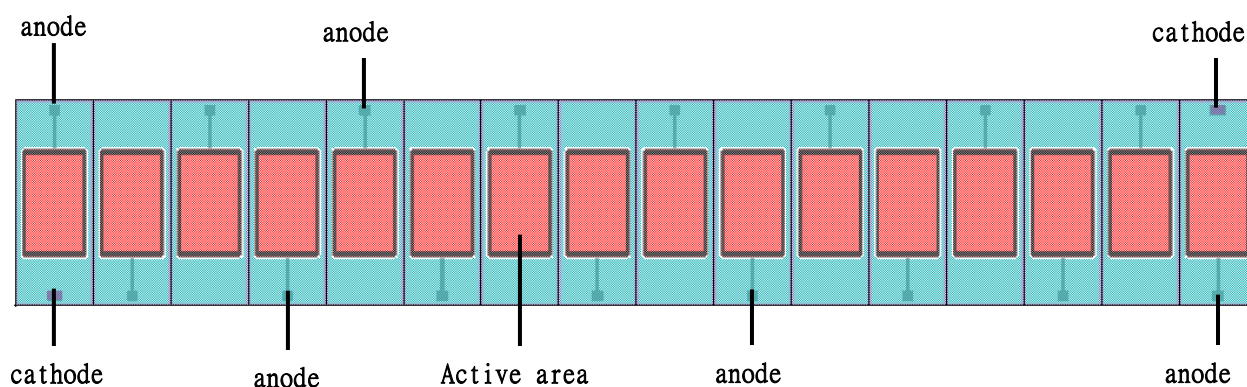
This specification applies to PIN silicon photodiode chips,
Device No. PD-30405-B.

2. Structure :

- 2-1. Planar type : PIN Diode.
- 2-2. Electrodes :
Top side (Anode) : Aluminum alloy.
Backside (Cathode) : Gold.
There are both anode and cathode on the top side.

3. Size :

- 3-1. Chip size(including scribe lane): 992.12 mils × 165.35 mils (25.200 mm × 4.200 mm).
- 3-2. Chip thickness : 12 ± 0.98 mils (0.305 ± 0.025 mm).
- 3-3. Active area :
46.26 mils × 78.74 mils × 16 elements (1.175 mm × 2.000 mm × 16 elements).
- 3-4. Bonding pad (Anode) :
7.87 mils × 7.87 mils × 16 elements (0.200 × 0.200 mm × 16 elements).
- 3-5. Bonding pad (Cathode) :
11.8 mils × 7.87 mils × 2 elements (0.300 × 0.200 mm × 2 elements).
- 3-6. Pattern drawing : Refer to the attached drawing.

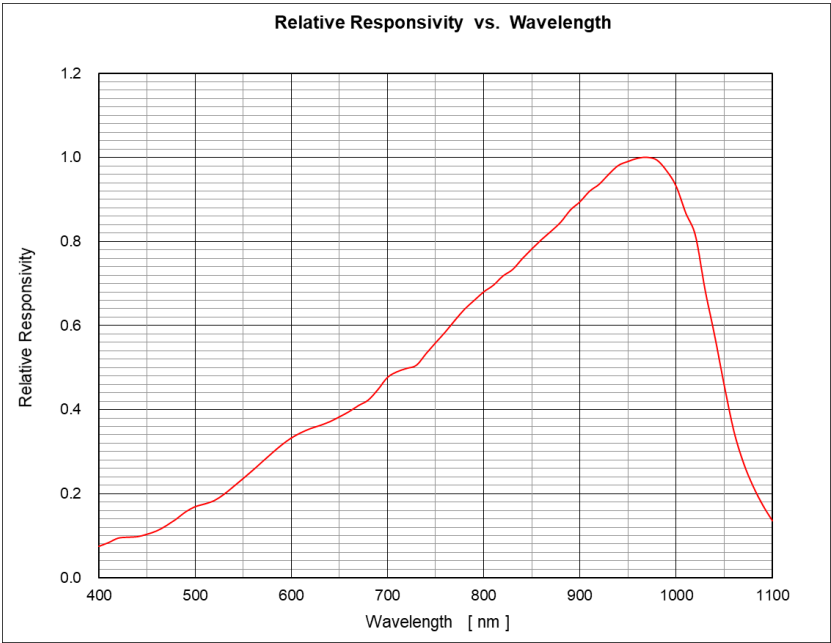


4. Electro-optical characteristics (Ta = 25 °C, single element)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
*Reverse dark current	I_D	VR=10V Ee=0mW/cm ²			10	nA
*Reverse breakdown voltage	V(BR)R	IR=100uA Ee=0mW/cm ²	60			V
*Forward Voltage	V _F	IF=20mA Ee=0mW/cm ²			1.2	V
Total Capacitance	C _t	VR =0V Ee=0mW/cm ² f=1MHz		33		pF

*Based on 100% probing

5. Relative spectral responsivity



^{*)} Bare chip measured with integrating sphere, for reference only.